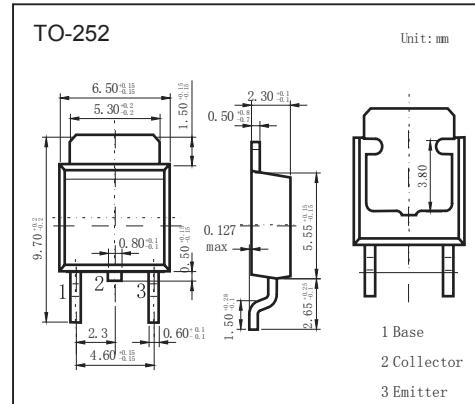


## PNP Transistors

### 2SB1172A

#### ■ Features

- High forward current transfer ratio hFE which has satisfactory linearity
- Low collector-emitter saturation voltage  $V_{CE(sat)}$
- Complementary to 2SD1742A



#### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CBO}$	-80	V
Collector - Emitter Voltage	$V_{CEO}$	-80	
Emitter - Base Voltage	$V_{EBO}$	-5	
Collector Current - Continuous	$I_C$	-3	A
Collector current -Pulse	$I_{CP}$	-5	
Collector Power Dissipation $T_a = 25^\circ\text{C}$	$P_C$	15	W
		1.3	
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature range	$T_{stg}$	-55 to 150	

#### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	$V_{CBO}$	$I_C = -100 \mu\text{A}, I_E = 0$	-80			V
Collector- emitter breakdown voltage	$V_{CEO}$	$I_C = -30 \text{ mA}, I_B = 0$	-80			
Emitter - base breakdown voltage	$V_{EBO}$	$I_E = -100 \mu\text{A}, I_C = 0$	-5			
Collector-base cut-off current	$I_{CBO}$	$V_{CB} = -80\text{V}, I_E = 0$			-0.1	mA
Collector-emitter cut-off current	$I_{CES}$	$V_{CE} = -80\text{ V}, I_B = 0$			-200	uA
Collector-emitter cut-off current	$I_{CEO}$	$V_{CE} = -60\text{ V}, I_B = 0$			-300	
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5\text{V}, I_C = 0$			-0.1	mA
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -3 \text{ A}, I_B = -375\text{mA}$			-1.2	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -3 \text{ A}, I_B = -375\text{mA}$			-1.5	
Base - emitter voltage	$V_{BE}$	$V_{CE} = -4\text{V}, I_C = -3 \text{ A}$			-1.8	
DC current gain	$h_{FE}$	$V_{CE} = -4\text{V}, I_C = -1 \text{ A}$	70		250	us
		$V_{CE} = -4\text{V}, I_C = -3 \text{ A}$	10			
Turn-ON Time	$t_{on}$	$I_C = -1 \text{ A}, I_{B1} = -100 \text{ mA}, I_{B2} = 100 \text{ mA}, V_{CC} = -50 \text{ V}$			0.5	us
Storage Time	$t_{stg}$				1.2	
Fall Time	$t_f$				0.3	
Transition frequency	$f_T$	$V_{CE} = -10\text{V}, I_C = -500\text{mA}, f = 10\text{MHz}$		30		MHz

#### ■ Classification of $h_{fe}(1)$

Type	2SB1172A-Q	2SB1172A-P
Range	70-150	120-250

## PNP Transistors

### 2SB1172A

#### ■ Typical Characteristics

